

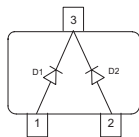
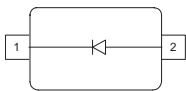
Silicon Tuning Diode

- Excellent linearity
- High Q hyperabrupt tuning diode
- Low series resistance
- High capacitance ratio
- Designed for low tuning voltage operation for VCO's in mobile communications equipment
- For control elements such as TCXOs and VCXOs



BBY57-02L
BBY57-02V
BBY57-02W

BBY57-05W



Type	Package	Configuration	L_S (nH)	Marking
BBY57-02L *	TSLP-2	single	0.4	55
BBY57-02V	SC79	single	0.6	5
BBY57-02W	SCD80	single	0.6	55
BBY57-05W	SOT323	common cathode	1.4	D5s

* Preliminary

Maximum Ratings at $T_A = 25^\circ\text{C}$, unless otherwise specified

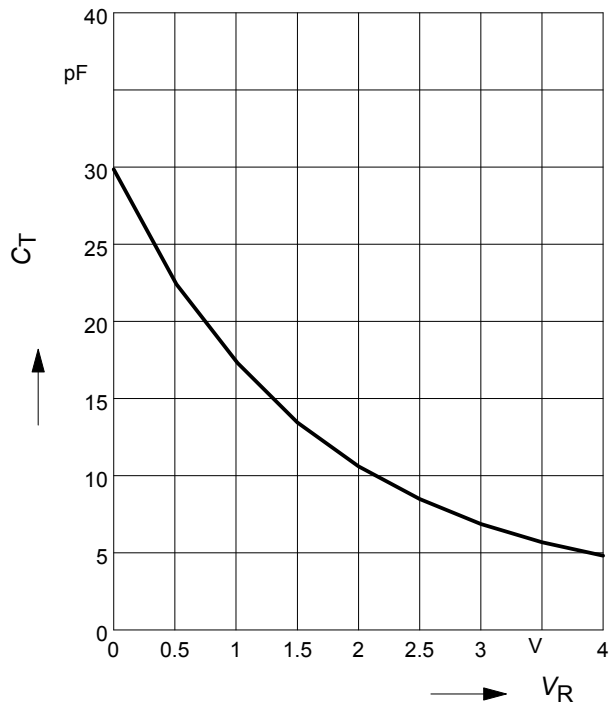
Parameter	Symbol	Value	Unit
Diode reverse voltage	V_R	10	V
Forward current	I_F	20	mA
Operating temperature range	T_{op}	-55 ... 125	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 ... 150	

Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics					
Reverse current	I_R				nA
$V_R = 8\text{ V}$		-	-	10	
$V_R = 8\text{ V}, T_A = 85\text{ }^{\circ}\text{C}$		-	-	100	
AC Characteristics					
Diode capacitance	C_T				pF
$V_R = 1\text{ V}, f = 1\text{ MHz}$		16.5	17.5	18.6	
$V_R = 2.5\text{ V}, f = 1\text{ MHz}$		-	9.35	-	
$V_R = 3\text{ V}, f = 1\text{ MHz}$		-	7	-	
$V_R = 4\text{ V}, f = 1\text{ MHz}$		3.5	4.7	5.5	
Capacitance ratio	C_{T1}/C_{T3}	-	2.45	-	
$V_R = 1\text{ V}, V_R = 3\text{ V}, f = 1\text{ MHz}$					
Capacitance ratio	C_{T1}/C_{T4}	3	3.7	4.5	
$V_R = 1\text{ V}, V_R = 4\text{ V}, f = 1\text{ MHz}$					
Series resistance	r_S				Ω
$V_R = 1\text{ V}, f = 470\text{ MHz}, \text{BBY57-02L}$		-	0.35	-	
$V_R = 1\text{ V}, f = 470\text{ MHz}, \text{all others}$		-	0.3	-	

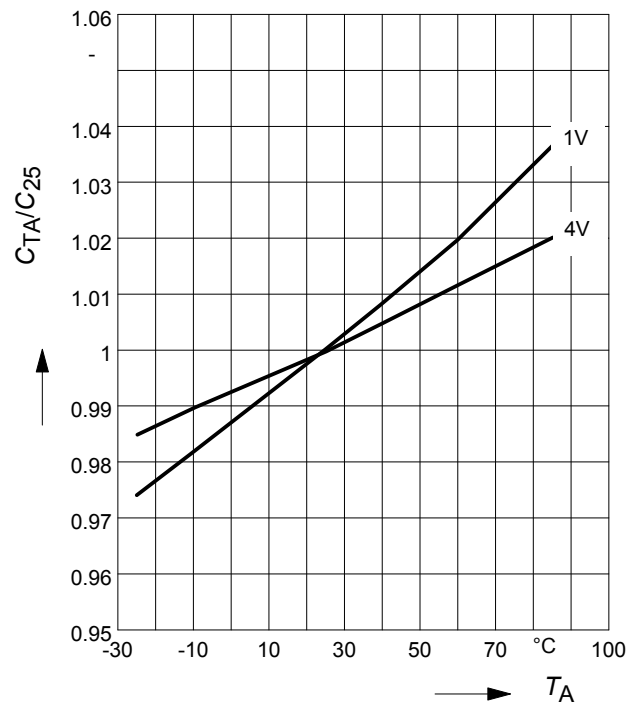
Diode capacitance $C_T = f(V_R)$

$f = 1\text{MHz}$



Normalized diode capacitance

$C_{(T_A)}/C_{(25^\circ\text{C})} = f(T_A); f = 1\text{MHz}$



Temperature coefficient of the diode capacitance $T_{CC} = f(V_R)$

